

# IPP80R900P7XKSA1

### IPP80R900P7XKSA1 Information

Heisener.com

**Part Number** IPP80R900P7XKSA1 **Manufacturer** Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 800V COOLMOS TO220-3

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

For Reference Only

Website: https://www.heisener.com
E-mail: salesdept@heisener.com

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## IPP80R900P7XKSA1 Specifications

Manufacturer Part Number         IPP80R900P7XKSA1           Manufacturer         Infineon Technologies           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         CoolMOS? P7           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         800V           Current - Continuous Drain (Id) @ 25°C         6A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         3.5V @ 110µA           Gate Charge (Qg) (Max) @ Vgs         15nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         350pF @ 500V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         45W (Tc)           Rds On (Max) @ Id, Vgs         900 mOhm @ 2.2A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO220-3           Package / Case         TO-220-3           Report errors?		
Category         Discrete Semiconductor Products           Package         TO-220-3           Series         CoolMOS? P7           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         800V           Current - Continuous Drain (Id) @ 25°C         6A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         3.5V @ 110μA           Gate Charge (Qg) (Max) @ Vgs         15nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         350pF @ 500V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         45W (Tc)           Rds On (Max) @ Id, Vgs         900 mOhm @ 2.2A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         PG-TO220-3           Package / Case         TO-220-3	Manufacturer Part Number	IPP80R900P7XKSA1
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SeriesCoolMOS? P7FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)800VCurrent - Continuous Drain (Id) @ 25°C6A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 110μAGate Charge (Qg) (Max) @ Vgs15nC @ 10VInput Capacitance (Ciss) (Max) @ Vds350pF @ 500VVgs (Max)±20VFET Feature-Power Dissipation (Max)45W (Tc)Rds On (Max) @ Id, Vgs900 mOhm @ 2.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3Package / CaseTO-220-3		Transistors - FETs, MOSFETs - Single
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 800V Current - Continuous Drain (Id) @ 25°C 6A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 110µA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 350pF @ 500V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 45W (Tc) Rds On (Max) @ Id, Vgs 900 mOhm @ 2.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package PG-TO220-3 Package / Case	Package	TO-220-3
Technology Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C 6A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 3.5V @ 110µA Gate Charge (Qg) (Max) @ Vgs 15nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max)  FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 900 mOhm @ 2.2A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Supplier Device Package PG-TO220-3 Package / Case  MOSFET (Metal Oxide)  800V  800V  800V  6A (Tc)  6A	Series	CoolMOS? P7
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Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package Package / Case  6A (Tc)  6A (	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO220-3  Package / Case  TO-220-3	Drain to Source Voltage (Vdss)	800V
Vgs(th) (Max) @ Id       3.5V @ 110μA         Gate Charge (Qg) (Max) @ Vgs       15nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       350pF @ 500V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       45W (Tc)         Rds On (Max) @ Id, Vgs       900 mOhm @ 2.2A, 10V         Operating Temperature       -55°C ~ 150°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       PG-TO220-3         Package / Case       TO-220-3	Current - Continuous Drain (Id) @ 25°C	6A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  +20V  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  Package / Case  15nC @ 10V  350pF @ 500V  +20V  +20V  FET Feature  -50°C ~ 150°C (TJ)  Through Hole  Through Hole	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  900 mOhm @ 2.2A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO220-3  Package / Case  TO-220-3	Vgs(th) (Max) @ Id	3.5V @ 110μA
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Rds On (Max) @ Id, Vgs900 mOhm @ 2.2A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackagePG-TO220-3Package / CaseTO-220-3	FET Feature	-
Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  PG-TO220-3  Package / Case  TO-220-3	Power Dissipation (Max)	45W (Tc)
Mounting Type Through Hole Supplier Device Package PG-TO220-3 Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	900 mOhm @ 2.2A, 10V
Supplier Device Package PG-TO220-3 Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	PG-TO220-3
Report errors?	Package / Case	TO-220-3
		Report errors?

#### IPP80R900P7XKSA1 Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### IPP80R900P7XKSA1 Payment Methods



















### IPP80R900P7XKSA1 Shipping Methods













If you have any question about IPP80R900P7XKSA1, please do not hesitate to contact us!

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